

## POWER SILICON RECTIFIER

Qualified per MIL-PRF-19500/162

### Devices

**1N1614**  
**1N1614R**

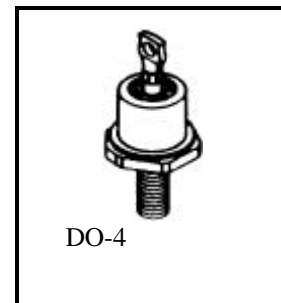
### Qualified Level

**JAN**  
**JANTX**

### MAXIMUM RATINGS

Ratings	Symbol	1N1614, R	Unit
Working Peak Reverse Voltage	$V_{RWM}$	200	Vpk
Average Forward Current	$I_O$	$T_C = +25^{\circ}C^{(1)}$	10
		$T_C = +150^{\circ}C$	5
Forward Current	$I_F$	15	Adc
Forward Current Surge Peak	$I_{FSM}$	100	A
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +175	$^{\circ}C$

1) Derate linearly 40 mA/ $^{\circ}C$  above  $T_C = +25^{\circ}C$



\*See appendix A for package outline

### ELECTRICAL CHARACTERISTICS ( $T_A = +25^{\circ}C \pm 3^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
Forward Voltage $t_p \leq 8.3$ ms, duty cycle $\leq 2.0\%$ pulsed; $I_F = 15$ A (pk)	$V_F$		1.5	Vpk
Reverse Current Leakage $V_R =$ Rated $V_{RWM}$	$I_R$		50	$\mu$ Adc
Thermal Impedance $I_M = 50$ to 250 mA; $I_H = 3$ to 10 Adc; $t_H = 150$ to 400 ms; $t_{MD} = 50$ to 300 $\mu$ s max	$Z_{\theta JX}$		4.5	$^{\circ}C/W$